

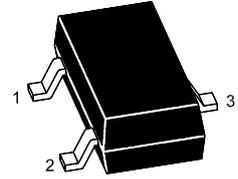
# MMBT3906

## PNP Transistor

### Features

- For Switching and AF Amplifier Applications.
- Silicon Epitaxial Chip.

**SOT-23**  
**(TO-236)**

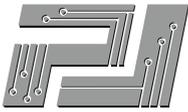


1.Base 2.Emitter 3.Collector

**Marking: 3E**

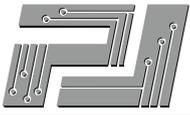
### Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ )

| Parameter                 | Symbol     | Value         | Unit             |
|---------------------------|------------|---------------|------------------|
| Collector Base Voltage    | $-V_{CBO}$ | 40            | V                |
| Collector Emitter Voltage | $-V_{CEO}$ | 40            | V                |
| Emitter Base Voltage      | $-V_{EBO}$ | 6             | V                |
| Collector Current         | $-I_C$     | 200           | mA               |
| Power Dissipation         | $P_D$      | 350           | mW               |
| Junction Temperature      | $T_J$      | 150           | $^\circ\text{C}$ |
| Storage Temperature Range | $T_{STG}$  | - 55 to + 150 | $^\circ\text{C}$ |

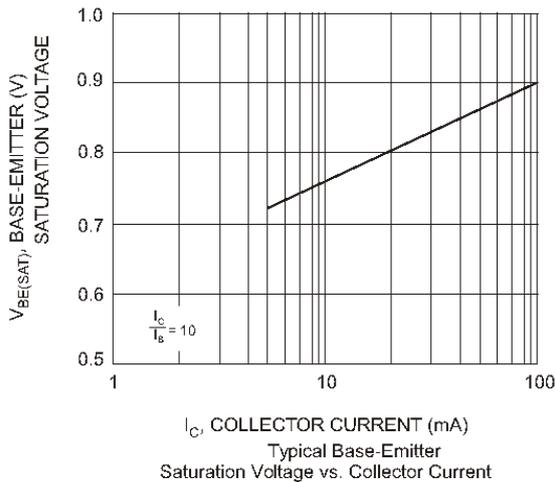
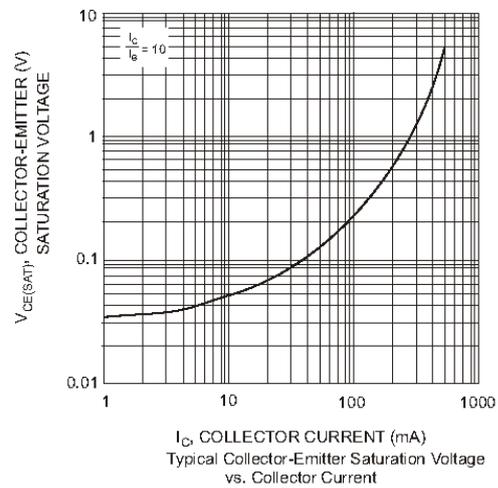
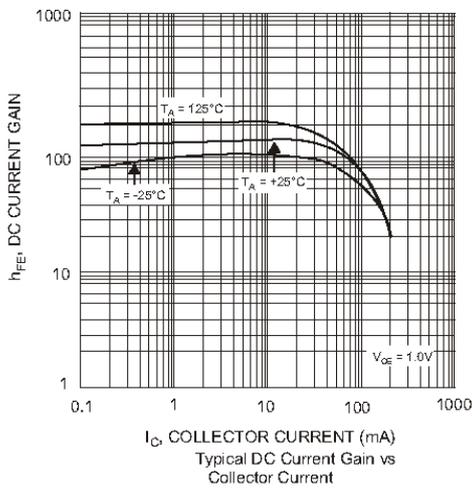
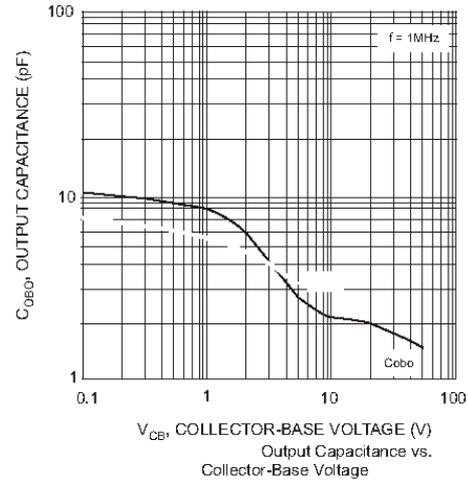
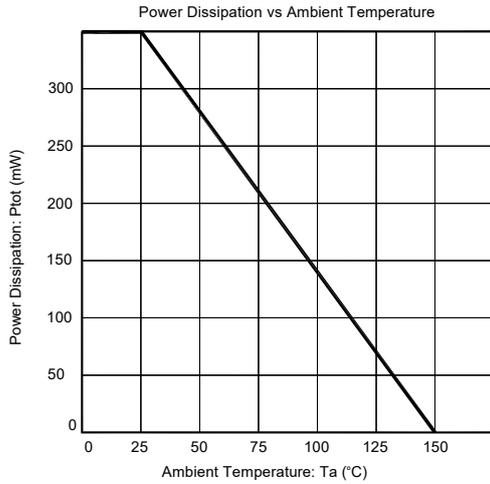


### Electrical Characteristics at $T_A = 25^\circ\text{C}$

| Parameter  | Symbol         | Min. | Max. | Unit |
|--|----------------|------|------|------|
| DC Current Gain<br>at $-V_{CE} = 1\text{ V}$ , $-I_C = 0.1\text{ mA}$  | $h_{FE}$       | 60   | -    | -    |
| at $-V_{CE} = 1\text{ V}$ , $-I_C = 1\text{ mA}$   | $h_{FE}$       | 80   | -    | -    |
| at $-V_{CE} = 1\text{ V}$ , $-I_C = 10\text{ mA}$  | $h_{FE}$       | 100  | 300  | -    |
| at $-V_{CE} = 1\text{ V}$ , $-I_C = 50\text{ mA}$  | $h_{FE}$       | 60   | -    | -    |
| at $-V_{CE} = 1\text{ V}$ , $-I_C = 100\text{ mA}$   | $h_{FE}$       | 30   | -    | -    |
| Collector Base Cutoff Current<br>at $-V_{CB} = 30\text{ V}$  | $-I_{CBO}$     | -    | 50   | nA   |
| Emitter Base Cutoff Current<br>at $-V_{EB} = 6\text{ V}$   | $-I_{EBO}$     | -    | 50   | nA   |
| Collector Base Breakdown Voltage<br>at $-I_C = 10\text{ }\mu\text{A}$  | $-V_{(BR)CBO}$ | 40   | -    | V    |
| Collector Emitter Breakdown Voltage<br>at $-I_C = 1\text{ mA}$   | $-V_{(BR)CEO}$ | 40   | -    | V    |
| Emitter Base Breakdown Voltage<br>at $-I_E = 10\text{ }\mu\text{A}$  | $-V_{(BR)EBO}$ | 6    | -    | V    |
| Collector Emitter Saturation Voltage<br>at $-I_C = 10\text{ mA}$ , $-I_B = 1\text{ mA}$                              | $-V_{CE(sat)}$ | -    | 0.25 | V    |
| at $-I_C = 50\text{ mA}$ , $-I_B = 5\text{ mA}$  | $-V_{CE(sat)}$ | -    | 0.4  | V    |
| Base Emitter Saturation Voltage<br>at $-I_C = 10\text{ mA}$ , $-I_B = 1\text{ mA}$                                   | $-V_{BE(sat)}$ | 0.65 | 0.85 | V    |
| at $-I_C = 50\text{ mA}$ , $-I_B = 5\text{ mA}$  | $-V_{BE(sat)}$ | -    | 0.95 | V    |
| Current Gain Bandwidth Product<br>at $-V_{CE} = 20\text{ V}$ , $-I_C = 10\text{ mA}$ , $f = 100\text{ MHz}$          | $f_T$          | 250  | -    | MHz  |
| Output Capacitance<br>at $-V_{CB} = 5\text{ V}$ , $I_E = 0$ , $f = 1\text{ MHz}$                                     | $C_{ob}$       | -    | 4.5  | pF   |
| Delay Time<br>at $-V_{CC} = 3\text{ V}$ , $-V_{BE} = 0.5\text{ V}$ , $-I_C = 10\text{ mA}$ , $-I_{B1} = 1\text{ mA}$ | $t_d$          | -    | 35   | ns   |
| Rise Time<br>at $-V_{CC} = 3\text{ V}$ , $-V_{BE} = 0.5\text{ V}$ , $-I_C = 10\text{ mA}$ , $-I_{B1} = 1\text{ mA}$  | $t_r$          | -    | 35   | ns   |
| Storage Time<br>at $-V_{CC} = 3\text{ V}$ , $-I_C = 10\text{ mA}$ , $-I_{B1} = I_{B2} = 1\text{ mA}$                 | $t_s$          | -    | 225  | ns   |
| Fall Time<br>at $-V_{CC} = 3\text{ V}$ , $-I_C = 10\text{ mA}$ , $-I_{B1} = I_{B2} = 1\text{ mA}$                    | $t_f$          | -    | 75   | ns   |

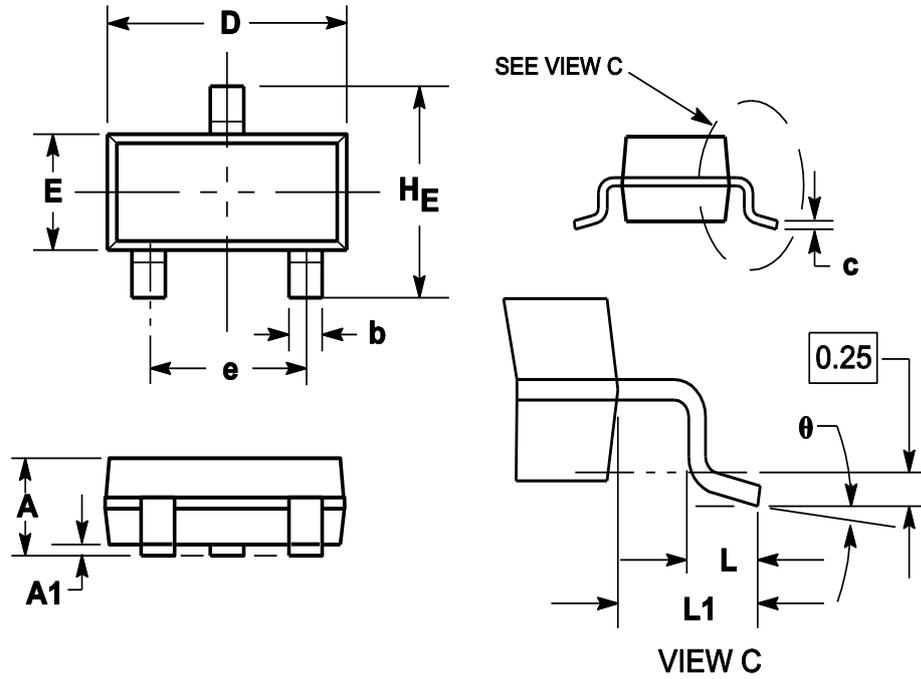


### Electrical Characteristics Curves





### Package Outline (SOT-23)



| Symbol   | Dimensions in millimeter |       |       |
|----------|--------------------------|-------|-------|
|          | Min.                     | Typ.  | Max.  |
| A        | 0.900                    | 1.025 | 1.150 |
| A1       | 0.000                    | 0.050 | 0.100 |
| b        | 0.300                    | 0.400 | 0.500 |
| c        | 0.080                    | 0.115 | 0.150 |
| D        | 2.800                    | 2.900 | 3.000 |
| E        | 1.200                    | 1.300 | 1.400 |
| HE       | 2.250                    | 2.400 | 2.550 |
| e        | 1.800                    | 1.900 | 2.000 |
| L1       | 0.550REF                 |       |       |
| L        | 0.300                    |       | 0.500 |
| $\theta$ | 0°                       |       | 8°    |

### Ordering Information

| Device   | Package | Reel Dimension (inch) | Shipping Quantity |
|----------|---------|-----------------------|-------------------|
| MMBT3906 | SOT-23  | 7                     | 3,000             |

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